## NSR15SDW1T1 <br> NSR15SDW1T2

## Dual RF Schottky Diode

These diodes are designed for analog and digital applications, including DC based signal detection and mixing applications.

## Features

- Low Capacitance ( $<1 \mathrm{pF}$ )
- Low $\mathrm{V}_{\mathrm{F}}(390 \mathrm{mV}$ typical @ 1 mA$)$
- Low $\mathrm{V}_{\mathrm{F} \Delta}$ (1 mV typical @ 1 mA )
- Pins 2 and 5 Shorted
- Pb -Free Packages are Available


## Benefits

- Reduced Parasitic Losses
- Accurate Signal Measurement
- Reduced Cross Talk


## MAXIMUM RATINGS

| Rating | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Peak Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 15 | V |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 30 | mA |
| Operating and Storage <br> Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| ESD Rating: Class 1 per Human Body Model <br> Class A per Machine Model |  |  |  |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Maximum Thermal Resistance <br> Junction-to-Ambient | $\mathrm{R}_{\theta \mathrm{JA}}$ | 500 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ON Semiconductor ${ }^{\circledR}$
http://onsemi.com

## RF SCHOTTKY BARRIER DIODES 15 VOLTS, 30 mA


SC-88
CASE 419B
STYLE 21

## MARKING DIAGRAM



R6 = Specific Device Code
M = Date Code

- = Pb-Free Package
(Note: Microdot may be in either location)


## ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| NSR15SDW1T1 | SC-88 | 3000/Tape \& Reel |
| NSR15SDW1T1G | SC-88 <br> (Pb-Free) | 3000/Tape \& Reel |
| NSR15SDW1T2 | SC-88 | 3000/Tape \& Reel |
| NSR15SDW1T2G | SC-88 <br> (Pb-Free) | 3000/Tape \& Reel |
| NSR15SDW1T4 | SC-88 | 10,000/Tape \& Reel |
| NSR15SDW1T4G | SC-88 <br> (Pb-Free) | 10,000/Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Min | Typ | Max |
| :--- | :---: | :---: | :---: | :---: |
| Unit |  |  |  |  |
| Breakdown Voltage $\left(\mathrm{I}_{\mathrm{R}}=10 \mu \mathrm{~A}\right)$ | $\mathrm{V}_{\mathrm{BR}}$ | 15 | 20 | - |
| Reverse Leakage $\left(\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}\right)$ | $\mathrm{I}_{\mathrm{R}}$ | - | 2 | 50 |
| Forward Voltage $\left(\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}\right)$ | $\mathrm{V}_{\mathrm{F} 1}$ | - | 390 | 415 |
| Forward Voltage $\left(\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}\right)$ | $\mathrm{V}_{\mathrm{F} 2}$ | - | 530 | 680 |
| Delta $\mathrm{V}_{\mathrm{F}}\left(\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}\right.$, All Diodes $)$ | $\Delta \mathrm{V}_{\mathrm{F}}$ | - | 1 | 15 mV |
| Capacitance $\left(\mathrm{V}_{\mathrm{F}}=0 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{T}}$ | - | 0.8 | 1 |



Figure 1. Forward Current versus Forward Voltage at Temperatures


Figure 3. Total Capacitance versus Reverse Voltage


Figure 2. Reverse Current versus Reverse Voltage


Figure 4. Dynamic Resistance versus Forward Current


Figure 5. Typical $\mathrm{V}_{\mathrm{F}}$ Match at Mixer Bias Levels


Figure 6. Typical $\mathrm{V}_{\mathrm{F}}$ Match at Detector Bias Levels


Figure 7. Typical Output Voltage versus Input Power, Small Signal Detector Operating at 850 MHz


Figure 8. Typical Output Voltage versus Input Power, Large Signal Detector Operating at 915 MHz


Figure 9. Typical Conversion Loss versus L.O. Drive, 2.0 GHz


RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 2. CONTROLLING DIMENSION: MILLIMETERS.
2. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
3. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DIMENSIONS D AND E1 AT THE OUT
THE PLASTIC BODY AND DATUM H.
THE PLASTIC BODY AND DATUM H.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND c APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
6. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | -- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |
|  | GENERIC |  |  |  |  |  |
|  | MARKING DIAGRAM* |  |  |  |  |  |



XXX $=$ Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


## STYLES ON PAGE 2

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## SC-88/SC70-6/SOT-363

CASE 419B-02
ISSUE Y
STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 19:
PIN 1. IOUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF
STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1
STYLE 2:

CANCELLED
STYLE 8:
CANCELLED

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR
STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAAN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

| STYLE 3 : CANCELLED | STYLE 4: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. ANODE | STYLE 5: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. CATHODE | STYLE 6 : <br> PIN 1. ANODE 2 <br> 2. $\mathrm{N} / \mathrm{C}$ <br> 3. CATHODE 1 <br> 4. ANODE 1 <br> 5. N/C <br> 6. CATHODE 2 |
| :---: | :---: | :---: | :---: |
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: |
| PIN 1. EMITTER 2 | PIN 1. SOURCE 2 | PIN 1. CATHODE 2 | PIN 1. ANODE 2 |
| 2. EMITTER 1 | 2. SOURCE 1 | 2. CATHODE 2 | 2. ANODE 2 |
| 3. COLLECTOR 1 | 3. GATE 1 | 3. ANODE 1 | 3. CATHODE 1 |
| 4. BASE 1 | 4. DRAIN 1 | 4. CATHODE 1 | 4. ANODE 1 |
| 5. BASE 2 | 5. DRAIN 2 | 5. CATHODE 1 | 5. ANODE 1 |
| 6. COLLECTOR 2 | 6. GATE 2 | 6. ANODE 2 | 6. CATHODE 2 |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. $\mathrm{N} / \mathrm{C}$ | 2. GND | 2. CH 1 | 2. ANODE |
| 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. N/C | 5. VBUS | 5. CH 2 | 5. CATHODE |
| 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 27: | STYLE 28: | STYLE 29: | STYLE 30: |
| PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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